



型号: B5817WS B5818WS B5819WS

肖特基二极管 SCHOTTKY DIODE

### 主要特性/Features

正向导通电压低 Low forward conduction voltage

环保护结构提供瞬态保护 The ring protection structure provides transient protection

极小的恢复时间 Minimal recovery time

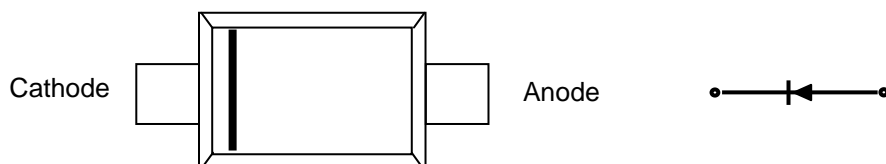
极小的恢复时间 Very small reverse capacitance

### 应用/Application

低压、高频等保护电路 High speed switch circuit

### 印字/MARKING 等效电路/Equivalent Circuit

型号	B5817WS	B5818WS	B5819WS
印章	<b>SJ</b>	<b>SK</b>	<b>SL</b>





极限参数/Absolute maximum ratings(Ta=25°C)

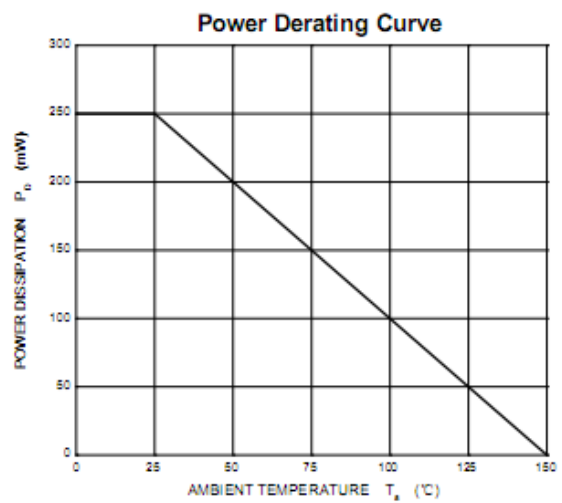
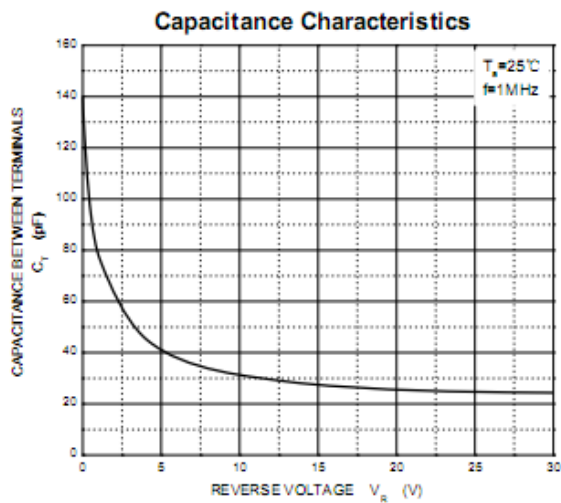
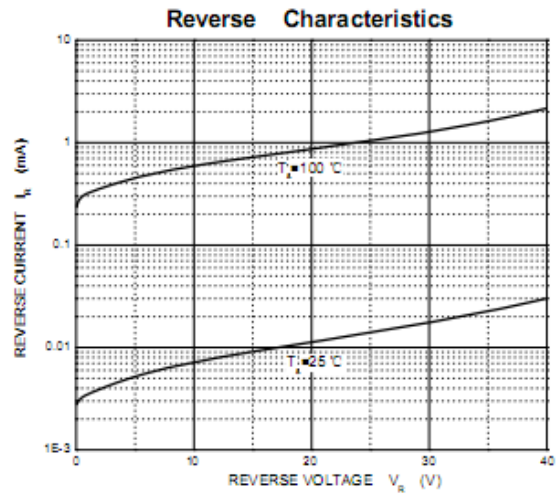
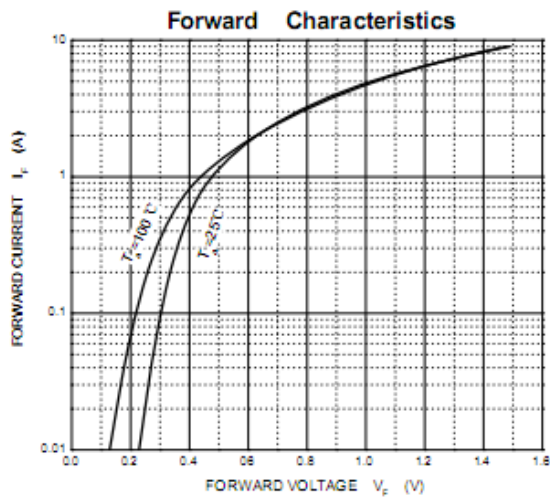
Parameter	Symbol	B5817WS	B5818WS	B5819WS	Unit
Non-Repetitive Peak Reverse Voltage	$V_{RM}$	20	30	40	
Peak Repetitive Peak Reverse Voltage Working PeakDC Blocking Voltage	$V_{RRM}$ $V_{RWM}$ $V_R$	20	30	40	V
RMS Reverse Voltage	$V_{R(RMS)}$	14	21	28	V
Average rectified output current	$I_O$	1			A
Peak Forward Surge Current (@t≤ 8.3mS)	$I_{FSM}$	9			A
Repetitive Peak Forward Current	$I_{FRM}$	1.5			A
Power Dissipation	$P_d$	250			mW
Thermal Resistance Junction To Ambient	$R_{\theta JA}$	500			°C /mW
Storage Temperature	Tstg	-55 ~ 150			°C

电性能参数/Electrical characteristics (Ta=25°C)

Parameter	Symbol	Test condition	MIN	TYP	Max	Unit
Reverse Breakdown Voltage B5817WS B5818WS B5819WS	$V_{(BR)}$	$I_R=1mA$	20 30 40			V
Forward Voltage	$V_F$	$I_F=1A$ B5817WS B5818WS B5819WS			0.45 0.55 0.6	V
		$I_F=3A$ B5817WS B5818WS B5819WS			0.75 0.875 0.9	V
Reverse voltage leakage current B5817WS B5818WS B5819WS	$I_R$	$V_R=20V$ $V_R=30V$ $V_R=40V$			1	mA
Diode Capacitance	$C_D$	$V_R=4V, f=1.0MHz$			120	pF

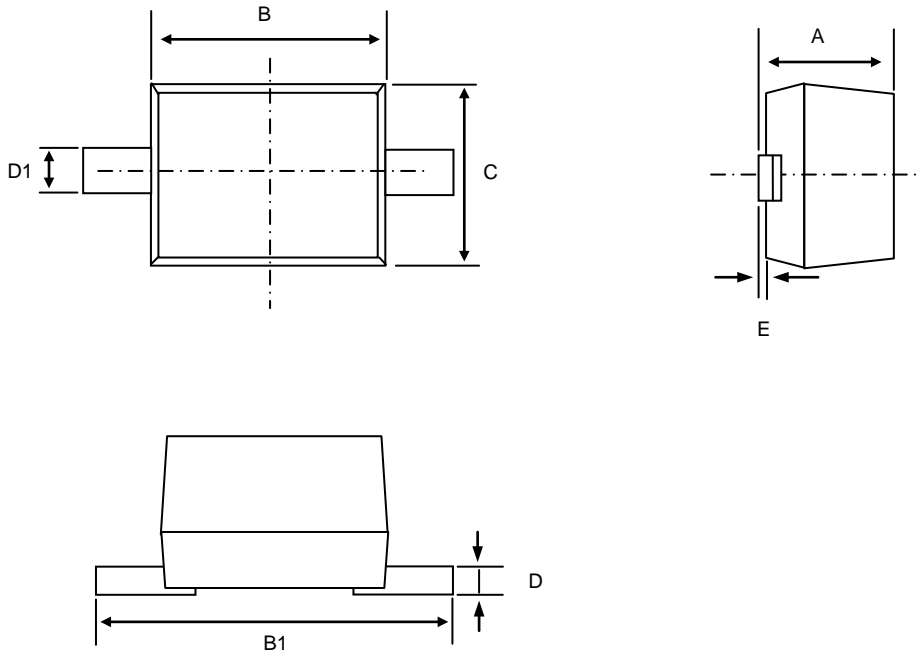


### 典型特性曲线图/Typical Characteristics





成品外观尺寸/SOD-323 Package Information



Symbol	Dim in mm		
	Min	Nor	Max
A	0.600	0.700	0.800
B	1.650	1.700	1.750
B1	2.250	2.600	2.750
C	1.250	1.300	1.350
D	0.100	0.110	0.120
D1	0.280	0.300	0.320
E	0.000	-	0.020